Amendments to the Specification:

Please replace the paragraph beginning on page 5, line 7, with the following rewritten paragraph:

However, if a plurality of batches of wafers are polished repeatedly using a four-way double-side polishing apparatus as described above or double-side polishing apparatus that ~~polishes~~ polish wafers by causing the carrier plate to make a circular motion not accompanied by its rotation, the polishing ability and other factors of polishing pads attached to the upper and lower turn tables change over time due to polishing pads' life, clogging and other factors. For this reason, polishing of a plurality of batches of wafers without replacement of the polishing pads has given rise to change in polished wafer shape over time with more polished batches, resulting in wafer shape differences between batches and problems that it is impossible to maintain wafer quality stably.

Please replace the paragraph beginning on page 6, line 23, with the following rewritten paragraph:

However, despite an attempt to control wafer shape by flowing cooling water, etc., through the turn tables and changing their temperature, the responsiveness of turn table deformation to varying turn table temperature (~~linearity~~ linearly relative to change in turn table temperature and the like) in conventional double-side polishing was poor, making it impossible to ensure high precision in the turn table shape control. Particularly if polishing conditions and the like are substantially changed during wafer polishing, there was caused a problem that it has been impossible to control the turn tables into a desired shape through the temperature control in the turn tables alone. When a plurality of batches of wafers are polished repeatedly, it has been difficult to control the turn table shape as desired with increasing number of wafer batches due to poor responsiveness of turn table deformation,

making it impossible to control batch-by-batch wafer shape stably and with high precision. In particular, repeated polishing of a plurality of batches of large-sized wafers such as 300mm-diameter wafers has often led to a convex wafer shape, thus exhibiting remarkably ~~deteriorations~~ deteriation of a wafer shape such that flatness of GBIR (Global Back Ideal Range), etc. is deteriorated. In other words, conventional turn table temperature control alone has failed to sufficiently control time-varying wafer shape.

Please replace the paragraph beginning on page 16, line 20, with the following rewritten paragraph:

To accomplish the ~~send~~ second object, according to the present invention, there is provided a wafer double-side polishing apparatus comprising at least a carrier plate having wafer holding holes; upper and lower turn tables to which polishing pads are attached; and a slurry supply means; with wafers held in the wafer holding holes, the carrier plate being moved between the upper and lower turn tables while supplying slurry, to simultaneously polish both front and back surfaces of wafers, wherein shape adjustment means are disposed at load supporting point portions of the upper turn table.

Please replace the paragraph beginning on page 31, line 13, with the following rewritten paragraph:

When wafers are repeatedly polished using a conventional double-side polishing apparatus as shown in Fig. 5, as the number of wafer batches to be polished increases it has become difficult to control the turn table shape with high precision due to poor responsiveness of turn table deformation (e.g., ~~linearity~~ linearly relative to changes in polishing conditions), making it impossible to control wafer shape stably and with high precision (first problem). Due to poor responsiveness of turn table deformation, it has been

impossible to precisely control the turn table into a desired shape with turn table temperature control alone, hindering stability and high precision in wafer shape control (second problem).

Please replace the paragraph beginning on page 37, line 27, with the following rewritten paragraph:

More specifically, the upper turn table 2 of the double-side polishing apparatus 1 is held to the housing 8 by the fixing means 9 such as ~~volts~~ bolts, with a given load applied during polishing. For this reason, load supporting points of the upper turn table 2 are located on the fixing means 9 that are joining portions between the upper turn table 2 and the housing 8 as shown in Fig. 2. Consequently, the PCD of upper turn table load supporting points can be expressed by a diameter 15 of a circle 16 joining the centers of the fixing means 9 that are the load supporting points of the upper turn table. The PCD of centers of the wafer holding holes on the carrier plate 6 can be, in the case of a double-side polishing apparatus with the single carrier plate 6 as described above, expressed by a diameter 18 of a circle 17 joining the centers of the wafer holding holes 19 (the centers roughly coincide with wafer centers of the wafers 4 held by the carrier plate 6) formed on the carrier plate 6 as shown in Fig. 3.

Please replace the paragraph beginning on page 48, line 24, with the following rewritten paragraph:

More specifically, the upper turn table 22 of the double-side polishing apparatus 21 is held to the housing 28 by the fixing means 29 such as bolts as ~~describes~~ described above. For this reason, load supporting points of the upper turn table 22 are located on the fixing means 29 that are joining portions between the upper turn table 22 and the housing 28. Consequently, the PCD of upper turn table load supporting points can be expressed by the diameter of the circle joining the centers of the fixing means 29 that are load supporting

points of the upper turn table. Since a plurality of wafer holding holes are formed on the carrier plates in such a double-side polishing apparatus, it is difficult to cause the average PCD of centers of wafer holding holes of the carrier plates (centers of wafers held by the carrier plates) to coincide with the PCD of upper turn table load supporting points. In the case of the double-side polishing apparatus 21, for this reason, the PCD of carrier plate centers that is the diameter of the circle joining centers of the plurality of carrier plates 26 is caused to coincide with the PCD of upper turn table load supporting points.